Abstracts

A 0.5 µm Silicon Bipolar Transistor for Low Phase Noise Oscillator Applications Up to 20 GHz

C.C. Leung, C.P. Snapp and V. Grande. "A 0.5 µm Silicon Bipolar Transistor for Low Phase Noise Oscillator Applications Up to 20 GHz." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 383-386.

An interdigitated silicon bipolar transistor with 0.5 micrometer emitter width and 2 micrometer emitter-emitter pitch has been fabricated which has a measured Fmax greater than 30 GHz. Low phase noise YIG-tuned oscillators with fundamental frequency bands of 4-18 and 8-22 GHz have been demonstrated using this transistor.

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